

Silicon N-Channel Super Junction Planar Power MOSFET

Description

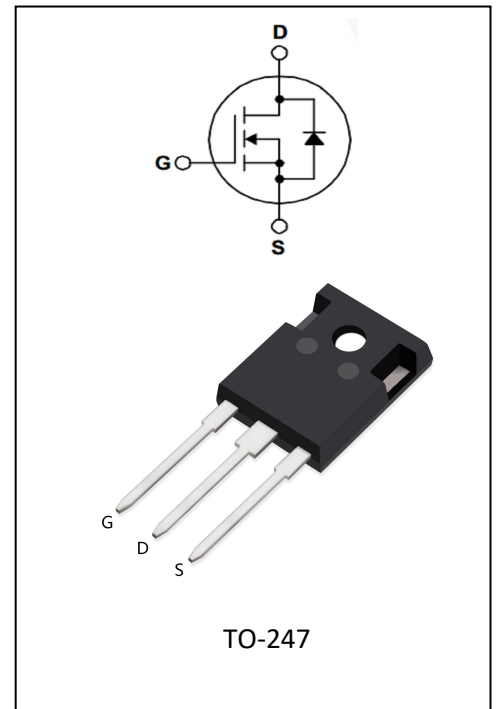
The TH65R090K utilizes the latest Super Junction processing techniques to achieve low on-resistance per silicon area. Additional features of this MOSFET are 150°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device. It can be used in a wide variety of applications.

General Features

- $V_{DS}=650V, I_D=47A$
- Low ON Resistance, $R_{DS(ON).max}=90m\Omega @ V_{GS}=10V, I_D=14A$
- Low reverse transfer capacitance
- Low Qg for fast response
- Short fall & rise times for fast switching
- 100% single pulse avalanche energy Test

Application

- Power switching application
- Digital amplifier
- Adapter and charger



Product Summary

V_{DS}	650V
$R_{DS(on).max}$	90m Ω
I_D	47A

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Continuous drain current $T_C = 25^\circ C$ (Silicon limit)	I_D	47	A
Pulsed drain current ($T_C = 25^\circ C$, t_p limited by T_{jmax})	I_{DM}	141	A
Avalanche energy, single pulse ($L=10mH$, $R_g=25\Omega$)	E_{AS}	1596	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ C$)	P_D	391	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ C$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case.	R_{thJC}	0.32	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	62	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	650	-	-	V	$V_{GS}=0V, I_D=10mA$
Gate threshold voltage	$V_{GS(th)}$	2.8	-	4.2	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 30V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.072	0.090	Ω	$V_{GS}=10V, I_D=14A$

Dynamic Characteristic

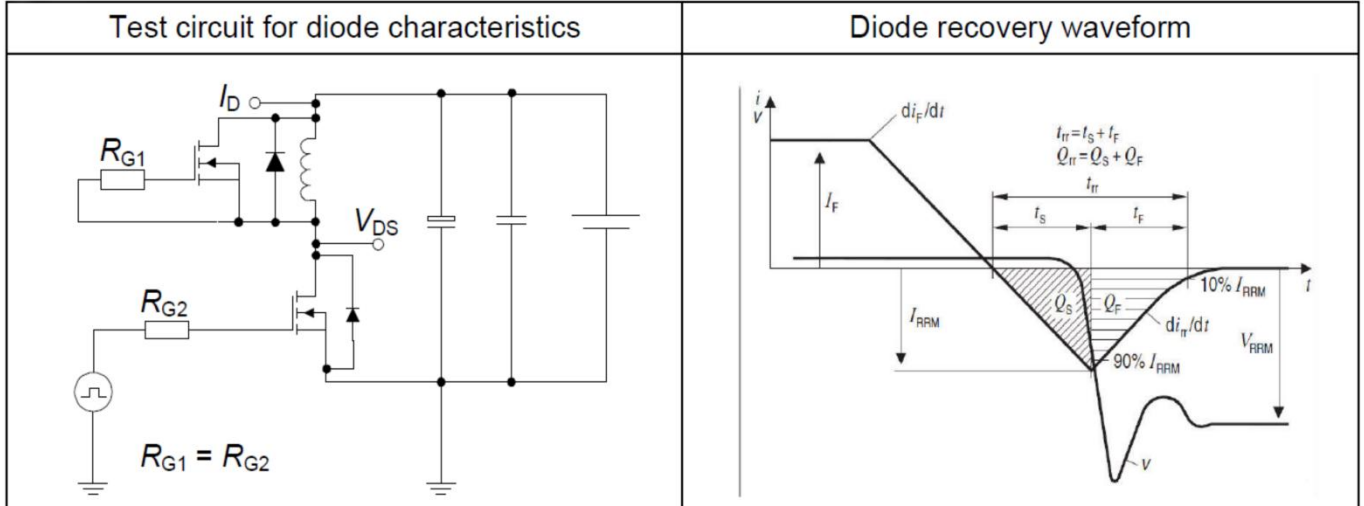
Input Capacitance	C_{iss}	-	4799	-	pF	$V_{GS}=0V, V_{DS}=50V,$ $f=10kHz$
Output Capacitance	C_{oss}	-	482	-		
Reverse Transfer Capacitance	C_{rss}	-	4.6	-		
Gate Total Charge	Q_g	-	82	-	nC	$V_{DD}=400V, I_D=25.8A$ $V_{GS}=0\text{ to }10V$
Gate-Source charge	Q_{gs}	-	18	-		
Gate-Drain charge	Q_{gd}	-	30	-		
Turn-on delay time	$t_{d(on)}$	-	38.8	-	ns	$V_{DD}=400V, V_{GS}=13V,$ $I_D=25.8A, R_G=1.7\Omega$
Rise time	t_r	-	26.8	-		
Turn-off delay time	$t_{d(off)}$	-	134.8	-		
Fall time	t_f	-	20	-		
Gate resistance	R_G	-	19	-	Ω	$f=1MHz, \text{open drain}$

Body Diode Characteristic

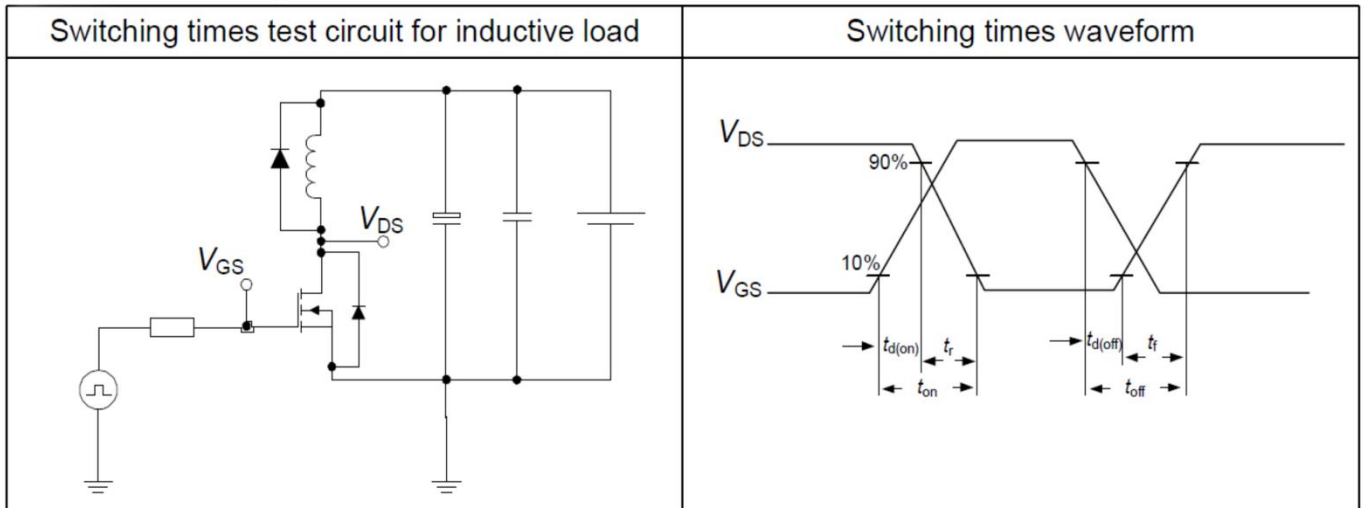
Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.69	-	V	$V_{GS}=0V, I_F=1A$
Body Diode Reverse Recovery Time	t_{rr}	-	436	-	ns	$V_R=400V, I_F=25.8A,$ $dI/dt=100A/us$
Body Diode Reverse Recovery Charge	Q_{rr}	-	7.6	-	μC	
Peak reverse recovery current	I_{rrm}	-	36		A	

Test Circuits

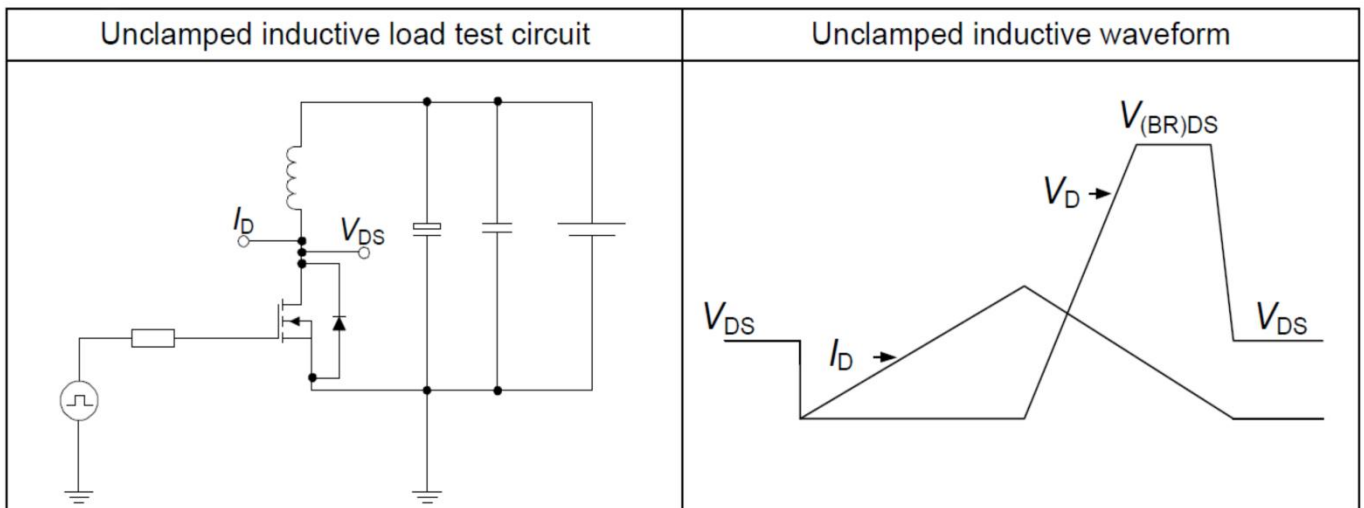
Diode characteristics



Switching times



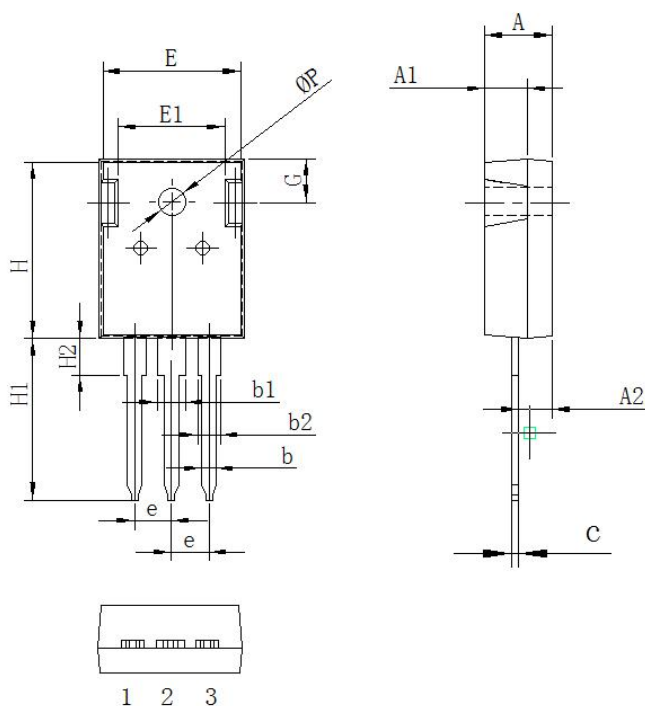
Unclamped inductive load



Package Information

TO-247 PACKAGE

基本尺寸



Symbol	单位 mm		
	Min	Nom	Max
A	4.8	5.00	5.20
A1	3.3	3.5	3.7
A2	2.20	2.40	2.60
b	1.00	1.2	1.40
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.2	15.7	16.2
E1	10.2	10.7	11.2
H	20.8	21	21.2
H1	19.5	20.0	20.5
H2	4.00	4.20	4.40
G	5.60	5.80	6.00
ΦP	3.50	3.70	3.90

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